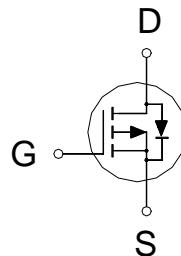


P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	-30V
R _{DSON} (MAX.)	125mΩ
I _D	-3.1A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _A = 25 °C	I _D	-3.1	A
	T _A = 70 °C		-2.1	
Pulsed Drain Current ¹		I _{DM}	-12	
Power Dissipation	T _A = 25 °C	P _D	1.04	W
	T _A = 70 °C		0.66	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Ambient ³	R _{θJA} (T ≤ 10sec)		83	°C / W
	R _{θJA} (Steady State)		120	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

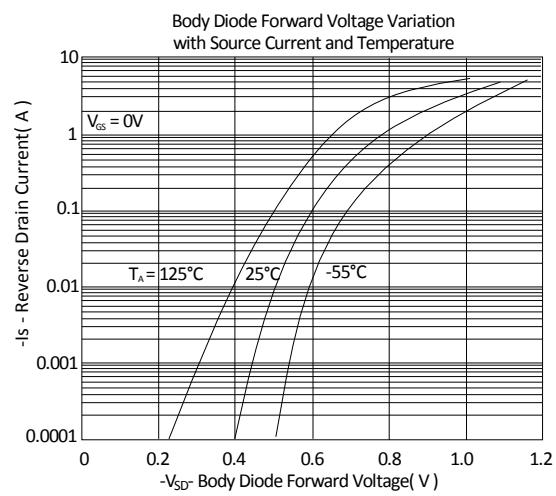
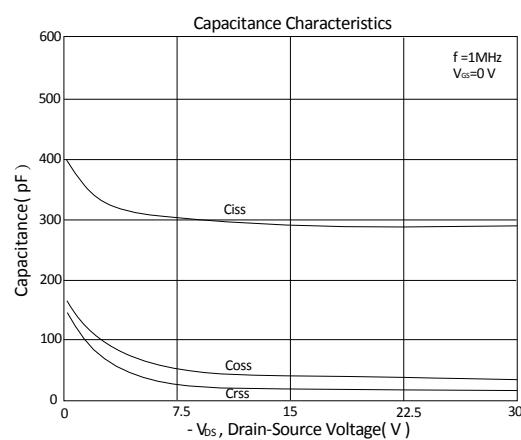
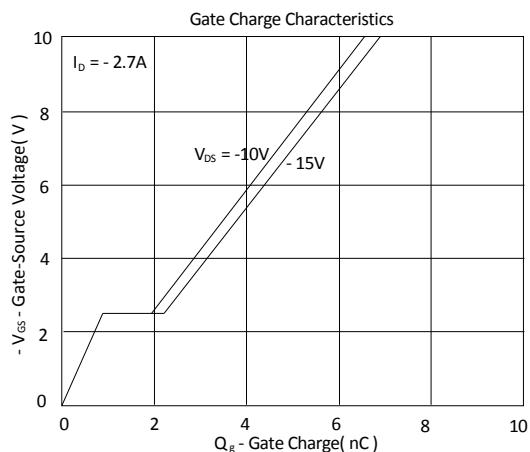
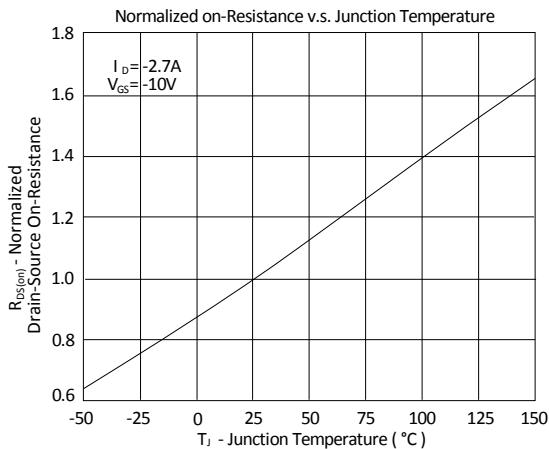
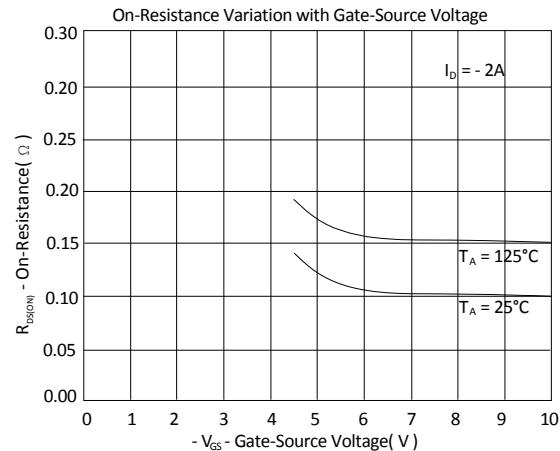
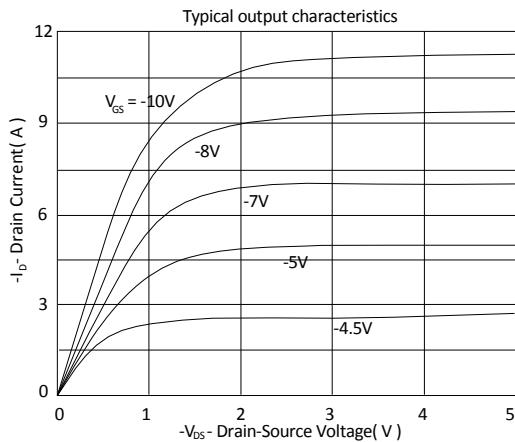
³The device mounted on a 1 in² pad of 2 oz copper.

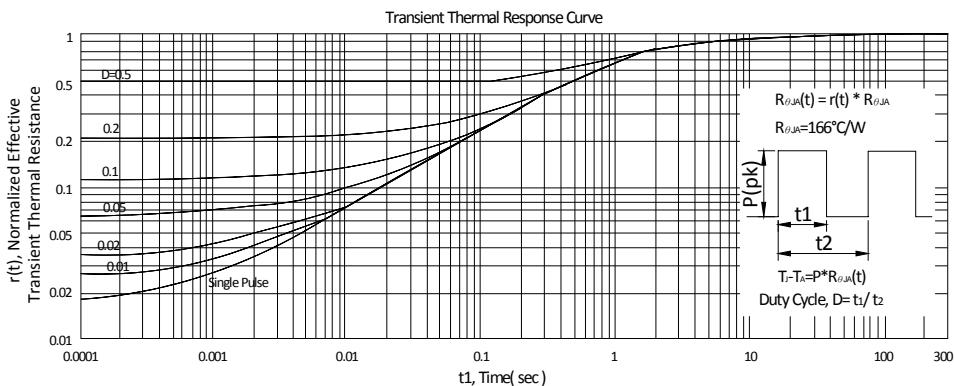
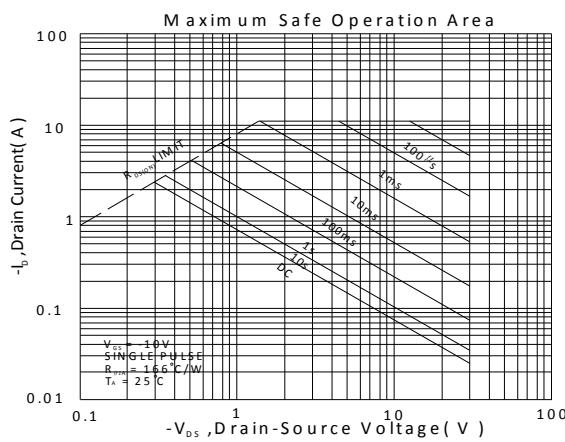
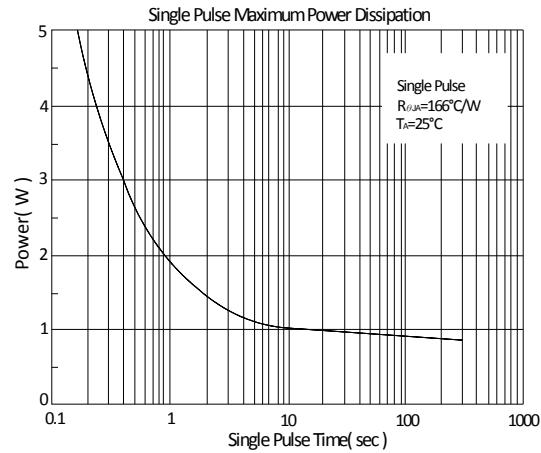
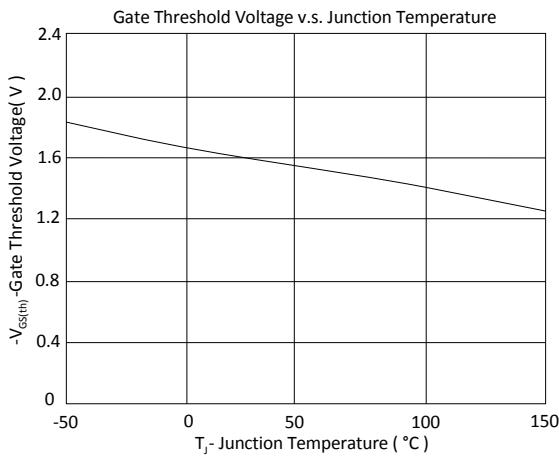
ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = -250\mu\text{A}$	-30			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.0	-1.6	-3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 125^\circ\text{C}$			-10	
On-State Drain Current ¹	$I_{D(\text{ON})}$	$V_{DS} = -5V, V_{GS} = -10V$	-3.1			A
Drain-Source On-State Resistance ¹	$R_{DS(\text{ON})}$	$V_{GS} = -10V, I_D = -3.1\text{A}$		100	125	$\text{m}\Omega$
		$V_{GS} = -4.5V, I_D = -2\text{A}$		140	190	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -5V, I_D = -3\text{A}$		4.5		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -15V, f = 1\text{MHz}$		294		
Output Capacitance	C_{oss}			41		pF
Reverse Transfer Capacitance	C_{rss}			24		
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -2.7\text{A}$		6.3		
Gate-Source Charge ^{1,2}	Q_{gs}			0.8		nC
Gate-Drain Charge ^{1,2}	Q_{gd}			1.4		
Turn-On Delay Time ^{1,2}	$t_{d(\text{on})}$	$V_{DS} = -15V,$ $I_D = -1\text{A}, V_{GS} = -10V, R_{GS} = 6\Omega$		10		
Rise Time ^{1,2}	t_r			20		nS
Turn-Off Delay Time ^{1,2}	$t_{d(\text{off})}$			15		
Fall Time ^{1,2}	t_f			12		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25^\circ\text{C}$)						
Continuous Current	I_S				-2	
Pulsed Current ³	I_{SM}				-8	A
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.2	V

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Pulse width limited by maximum junction temperature.

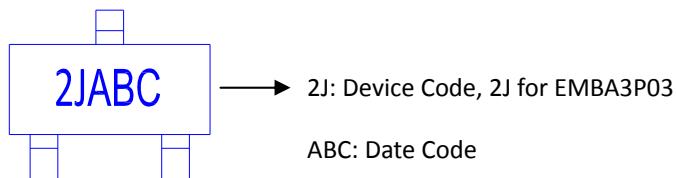
TYPICAL CHARACTERISTICS



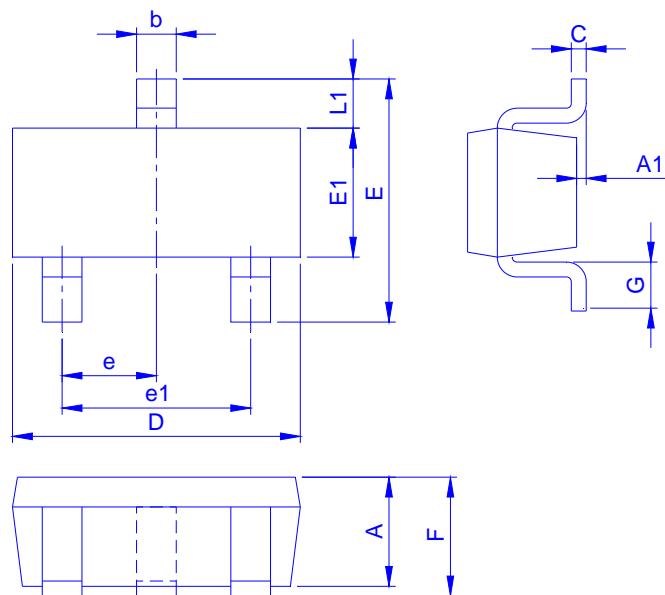


Ordering & Marking Information:

Device Name: EMBA3P03JS for SOT-23



Outline Drawing



Dimension in mm

Dimension	A	A1	b	C	D	E	E1	e	e1	F	G	L1
Min.	0.70	0	0.3	0.08	2.80	2.25	1.2	0.90		0.80	0.3	0.50
Typ.					2.90			0.95	1.9			
Max.	1.15	0.1	0.5	0.20	3.02	3.00	1.7	1.00		1.25	0.6	0.75

Footprint

